

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	4	metal adj gate and gate adj insulating adj layer and capping adj layer	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/10 11:54
S2	43	metal adj gate and gate adj oxide and capping adj layer	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/08 14:09
S3	7	metal adj gate and capping adj layer and selective adj oxidation	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/08 14:37
S4	30	metal adj gate and capping adj layer and oxid\$7 same silicon adj substrate	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/08 14:55
S5	6	metal adj gate and capping adj layer and oxidizing same silicon adj substrate	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/08 15:48
S6	2	metal adj gate and capping adj layer and selective adj oxidation same silicon adj substrate	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/09 12:31
S7	7	gate and capping adj layer and selective adj oxidation same silicon adj substrate	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/08 17:37
S8	9	("5573961"   "5631179"   "5736455"   "5766998"   "5851927"   "5869359"   "6075274"   "6136658"   "6162741").PN.	USPAT	OR	OFF	2004/11/08 16:53
S9	17	gate and capping adj layer and selective adj oxidation	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/08 17:37
S10	20	metal adj gate and selective adj oxidation same silicon adj substrate	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/09 12:49
S11	8	metal adj gate and selective adj oxidation same silicon adj substrate and "H.sub.2 O" and "H.sub.2"	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/09 12:40

S12	2	("4505028").PN.	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/09 12:54
S13	15	metal adj gate and silicon adj oxide adj layer and selective adj oxidation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/10 13:03
S15	118	gate and capping adj layer and selective near5 oxid\$7	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/15 11:26
S16	55	gate and capping adj layer and selective near5 oxid\$7 and silicon adj oxide	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/15 12:42
S17	25	gate and capping adj layer same silicon adj oxide and selective near5 oxid\$7	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/15 14:52
S18	638	Metal adj gate and source/drain adj region	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/15 14:54
S19	318	Metal adj gate and source/drain adj region and oxidation	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/15 14:55
S20	17	Metal adj gate and source/drain adj region and reoxidation	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/15 17:58
S21	245	"100" adj nm and metal adj gate and width	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/15 18:03
S22	3	"100" adj nm same metal adj gate same width	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/15 18:16
S23	5	"100" adj nm same metal adj gate same width	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/15 18:17
S24	2	("6277722").PN.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/05 10:43

S25	2	("4505028").PN.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/05 11:17
S26	2	("6245605").PN.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/05 11:18
S27	2	("6245605").PN.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/11 18:58